Reliable post-processing improvement of van der Waals heterostructures

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The successful assembly of heterostructures consisting of several layers of different 2D materials in arbitrary order by exploiting van der Waals forces has truly been a game changer in the field of low dimensional physics. For instance, the encapsulation of graphene or MoS$_2$ between atomically flat hexagonal boron nitride (hBN) layers with strong affinity and graphitic gates that screen charge impurity disorder provided access to a plethora of new physical phenomena by drastically boosting the device quality. The encapsulation is accompanied by a self-cleansing effect at the interfaces. The otherwise predominant charged impurity disorder is minimized and random strain fluctuations ultimately constitute the main source of residual disorder. Despite these advances, the fabricated heterostructures still vary notably in their performance and many possess only mediocre quality. Here, we report a reliable method to improve fully completed van der Waals heterostructure devices with a straightforward post-processing surface treatment based on contact mode AFM. The impact is demonstrated by comparing magnetotransport measurements before and after the AFM treatment on one and the same device as well as on a larger set of treated and untreated devices to collect device statistics. Both the low temperature properties as well as the room temperature electrical characteristics as relevant for applications improve on average substantially. We surmise that the main beneficial effect arises from reducing nanometer scale corrugations at the interfaces and, hence, the detrimental impact of random strain fluctuations due to the AFM ironing action.

**Keyword:** van der Waals heterostructure, graphene, molybdenum disulfide, quantum Hall effect, Hall sensor
The study of two dimensional electron systems with extraordinarily low levels of disorder was for a long time the exclusive privilege of the epitaxial thin film research community. The successful isolation of graphene by mechanical exfoliation [1] and its dramatic quality improvements through suspension [2, 3] or encapsulation [4] has however been truly disruptive. Even the most fragile ground states in two-dimensional electron physics have been unveiled in graphene and also new territory has been charted with for instance the observation of a superconducting ground state and previously unknown fractional quantum Hall states [5, 6, 7, 8, 9, 10]. A plethora of other two dimensional materials has also been successfully isolated with rapid progress in sample quality as well.

The exfoliation technique appears the best route to obtain devices with very low intrinsic defect density and the performance of the 2D crystals is mainly limited by extrinsic disorder such as for example charged impurities located in the environment surrounding the 2D lattice. Intense efforts have been made to optimize the device fabrication and handling routines in order to reduce these extrinsic sources of disorder. The so-called dry pick-up method that makes use of the van der Waals forces between the layered materials, has become the key enabler for building arbitrary heterostructures of high quality for various reasons [4]. For one, by encapsulating the studied 2D material, for instance graphene or MoS$_2$, in between a van der Waals material with a high affinity to the active layer a self-cleansing effect occurs at the hetero-interfaces causing an aggregation of the contaminants into randomly distributed bubbles [11]. The remaining, bubble-free area of the heterostructure possesses atomically clean interfaces [12]. The bubble density itself can be reduced significantly by increasing the temperature during the stacking procedure [13, 14] and subsequently performing annealing steps [15, Section 1 of SI]. The available area for designing high quality devices is then increased substantially. Hexagonal boron nitride (hBN) constitutes the candidate par excellence for encapsulation [16]. It combines a high affinity to graphene with a low intrinsic charged defect density [11, 17]. The addition of graphitic gates in these van der Waals heterostructures also aids by screening charged impurity disorder in the substrate [8, 18].

As charged impurity disorder is effectively minimized, another culprit takes over the scene. In a conclusive study, Couto and co-workers have demonstrated that random strain fluctuations make up the main source of residual disorder in already high quality graphene samples, e.g. on hBN [19]. In the low temperature limit, the mobility and the density inhomogeneity at low density, as estimated from the width of the field effect resistivity peak, are closely correlated. This finding can only be accounted for when random in-plane and out-of-plane deformations of the graphene lattice are the main source of long range disorder. Hence, the atomic flatness of hBN [16] or other van der Waals layers supporting the active layer under study plays a crucial role.

Despite all these measures, not all van der Waals heterostructures are created equal and a substantial variation among fabricated devices persists. Only a limited number does convincingly show the most fragile correlated ground states that can be anticipated in ultraclean 2D electron systems. Others only have mediocre quality and are usually not considered for further
measurements. It is a matter of statistics. Achieving an improved yield for excellent quality devices therefore remains an important goal. In this Letter, we report a reliable method to boost the quality of such van der Waals heterostructures by means of a final step subsequent to the device processing. It is based on scanning an atomic force microscope (AFM) tip, operated in contact mode with a well-defined force, across the active device area preselected based on the absence of bubbles in optical microscopy and non-contact AFM. The AFM tip efficiently cleans the top hBN surface from residues, which may act as a source of remote charged impurities. However, we surmise that the main beneficial effect arises from ironing away nanometer scale corrugations at the interfaces. This reduces the random strain fluctuations. Meanwhile we have applied this method to a multitude of fabricated devices and consistently obtain a higher yield of samples with enhanced properties, both statistically in terms of numbers as well as when making a comparison on one and the same device before and after the mechanical ironing procedure.

This Letter is organized as follows. We start with a detailed description of the heterostructure fabrication routine and the post-processing AFM treatment. To prove unambiguously its beneficial impact, low temperature magnetotransport measurements before and after the ironing are carried out on heterostructures consisting either of a graphene monolayer or a MoS$_2$ few layer, encapsulated in between thicker hBN flakes. We demonstrate that in some cases residues on the top hBN surface are removed and swept to the border of the scanning area, while in other instances no topographical changes are recorded at all in subsequent contactless AFM measurements. The working hypothesis, that an ironing-like effect may occur, is supported manipulating and displacing larger AFM detectable bubbles with the tip. Finally, room temperature transport properties on another graphene device (G2) are discussed in detail. We provide some statistics on the performance of a larger set of devices as relevant for Hall sensing and thereby demonstrate that the ironing technique also enhances notably application relevant room temperature properties.

All presented heterostructures were assembled with the dry van der Waals stacking method using a polymer stamp for the pick-up process and hBN flakes as encapsulating layers [4, 11]. The polymer of the stamp was varied in order to increase the possible temperature range for the pick-up and release process as this range is set by the polymer’s glass transition temperature. In general, a higher temperature improves the pick-up yield and also reduces the number of bubbles [11, 13]. A poly-propylene carbonate (PPC)/PDMS, a commercial viscoelastic film (PF film from Gel-Pak), as well as an elvacite resin [20, 21, 22, 23] were utilized. In cases where graphene is the active device layer, the stacks were annealed at 500°C in a forming gas (Ar/H$_2$) atmosphere after completed assembly and prior to further device processing. The purpose of the annealing is to lower the bubble density and increase the useable device area (see Fig. S1). We note that the stamp material did not affect the device quality nor the achievable improvement from the AFM treatment. However, the annealing step at 500°C turned out crucial to obtain a significant enhancement with AFM ironing (see Fig. S2). After this first annealing step, optical microscopy and non-contact AFM measurements were deployed to identify an area for the
device design exhibiting neither bubbles nor wrinkles with these two methods. The device fabrication steps entailed etch mask and contact patterning using electron beam lithography with PMMA resist. Etching was performed with a CHF$_3$/O$_2$ mixture in an Oxford ICP machine [22, 23]. Cr/Au edge contacts were thermally evaporated. A final annealing step at 350°C reduced the polymer residues from the device processing on the top of the hBN layer.

While the above processing routine was used for all graphene based van der Waals heterostructures, minor modifications were necessary for the MoS$_2$ devices. To avoid a degradation of the MoS$_2$ crystal, the annealing temperature after assembly was lowered from 500°C down to 350°C. Buried metal contacts (M1) instead of edge contacts were chosen in order to obtain lower contact resistances. The buried contacts were achieved by etching the bottom hBN flake separately and depositing a metallic layer with a thickness approximately equal to the etch depth. This guarantees that only a limited amount of strain is induced in the MoS$_2$ layer. The device fabrication was then completed by releasing the pre-assembled and annealed van der Waals heterostructure consisting of a hBN/graphite/hBN/MoS$_2$ stack (from top to bottom) onto the hBN layer with buried contacts. The graphite layer served as a top gate. For all other devices presented in this work a doped silicon back gate was used instead to tune the carrier density.

Magnetotransport measurements, conducted on these finished devices prior to AFM cleaning, served as a reference. The AFM cleaning was performed with a commercial system (NX-10 from Park Systems) operating in contact mode with a tip force between 50 and 150 nN and a scan speed between 0.3 and 0.6 Hz, although the mounted AFM tip is normally intended for non-contact mode measurements (Park PPP-NCHR). The entire device channel was treated with the tip. Non-contact AFM measurements were done before and after contact mode cleaning. Low temperature magnetotransport data recorded on a graphene stack (device G1) prior to tip cleaning are plotted in red color in panels a through c of Fig. 1. The curves reveal poor transport quality. A broad and asymmetric Dirac peak is observed and the mobility is only about 40,000 cm$^2$/Vs. The longitudinal resistance does not drop to zero in the quantum Hall regime, quantum oscillations are poorly visible and the plateaus in the Hall resistance are only reasonably developed for holes. Typically, one would sort out this device and fabricate another one. Instead, the sample was treated with the AFM tip and afterwards the transport measurements were repeated (black curves in Fig. 1). The width of the Dirac peak in the resistivity trace has shrunk substantially. Its position is now close to $V_g = 0$ V and the mobility is significantly enhanced to 350,000 cm$^2$/Vs. In the quantum Hall regime, the longitudinal resistance shows well developed quantum oscillations and nearly approaches zero. Hall plateaus are better developed and more numerous even at magnetic fields down to 1T.

This straightforward method to improve the magnetotransport properties is also effective on van der Waals heterostructures possessing an active layer other than graphene. Fig. 2 illustrates magnetotransport data recorded on an encapsulated few layer MoS$_2$ device (M1) at a density of 5 $\times$ 10$^{12}$ cm$^{-2}$. An optical image of the device is shown in the inset to panel a. The red and black traces have been acquired before and after AFM cleaning, respectively. Panel a shows the raw
data across the entire magnetic field range, while an enlarged window focusing on the low magnetic field regime is displayed in panel b. Prior to AFM cleaning, Shubnikov-de Haas oscillations develop around $B = 2.5$ T and signatures of incompressible symmetry broken ground states due to degeneracy lifting are observed at much higher magnetic fields only. After AFM cleaning, the quantum oscillations are much better developed and the onset is shifted downwards to $B = 1.7$ T. Additional quantum oscillations due to symmetry breaking are visible from $B = 2.5$ T onwards. We emphasize that this substantial improvement of the electronic quality has been achieved solely by post-processing AFM cleaning.

In an attempt to identify possible reasons for the sample quality improvement, we have analyzed the AFM images recorded in non-contact mode before and after tip cleaning. An example is illustrated in Fig. 3b. In the left image, the channel of this device was already free of bubbles and wrinkles before the AFM cleaning procedure, at least within the resolution of conventional AFM. Yet, contrary to expectation, the transport quality as discussed previously was poor. Some residues are visible on the top hBN surface. These residues were mechanically removed during the contact mode AFM scan as seen in the right image in Figure 3b. The surface of the top hBN layer becomes flatter as highlighted in Figure 3b and d. This mechanical residue cleaning is however likely not the cause of the substantial improvement in device quality. In contrast to earlier reports on a slight performance gain due to the mechanical cleaning of uncovered graphene [24, 25], the conducting 2D material under test is completely sandwiched by thicker hBN layers. Therefore, the residues are not in direct contact and should not constitute a major source of disorder. Indeed, a former study on graphene based van der Waals heterostructures revealed that encapsulated graphene is essentially insensitive to polymer residues and the device performance was reported to be identical with and without polymer residues [4]. Moreover, some investigated devices were already sufficiently clean and did not show an accumulation of residues on top of the hBN cap layer. Yet, they still consistently benefited from AFM cleaning.

Our working hypothesis is that the AFM tip is capable of mechanically manipulating the buried interfaces and abating local sub-nanometer corrugations of these interfaces. This scenario would offer an immediate and plausible explanation for the observed improvement in the electrical transport characteristics of the AFM treated devices. As mentioned before, local strain fluctuations have been spotted as an important remaining source of long range extrinsic disorder limiting the quality in otherwise very clean van der Waals heterostructures [19]. If the act of scanning the AFM tip across the top surface of the heterostructure is equivalent to ironing out sub-nanometer local roughness, local strain fluctuations would be mitigated and the transport quality improved. In order to demonstrate that mechanical manipulation of interfacial roughness is in principle possible, we have applied the ironing procedure to other areas that exhibit larger, AFM detectable bubbles. The force needed to move those bubbles appears to scale with their lateral dimensions. An example of a heterostructure with three micrometer sized pockets, marked as A, B, and C, is shown in Figure 3e. After contact mode tip scanning, pocket A disappeared, i.e. likely ruptured, while B and C moved in the direction of the scan. However, we find the success
rate of moving micrometer size bubbles by means of an AFM tip to be very low. The majority of the bubbles larger than one micrometer in size remain at their position even when forces up to several thousand nN are applied as shown in Figure 3e and f. The applied force more likely rips apart the bubble thereby damaging the heterostructure [12]. In this work, much smaller bubbles or interfacial roughness with sub-nanometer thickness are relevant and small forces on the order of 100 nN may be sufficient to manipulate and flatten the interfaces reliably. After all, other groups have demonstrated little friction among the different layers of van der Waals heterostructures, e.g. graphene and hBN, so that local relative motion may occur and be enforced. For instance, thermal annealing can induce a rotation and sliding of graphene between two hBN flakes [26]. Single constituents of a heterostructure have also been twisted in-situ by an AFM tip [27]. While plausible, the flattening of sub-nanometer scale roughness and the accompanying release of in-plane strain fluctuations at the interfaces between the active 2D material and the hBN protective layer can unfortunately not be quantified directly, since conventional AFM does not allow observing sub-nanometer height changes at an interface buried by a hBN cap layer of at least a few nanometer. Other techniques to analyze the interfacial roughness are either destructive, restricted to areas of a few nanometer only or are insufficiently sensitive [12, 28]. Even if so, it is possible to indirectly corroborate that the AFM cleaning action is equivalent to ironing and local strain reduction. Following the procedure of Couto et al. [19], we estimated the residual total carrier density at the CNP \( n_{t,0} \), comprising the disorder induced electron hole puddles at low temperature, by a graphical analysis in a double-logarithmic plot of the conductivity as a function of density (see Figure S3). Subsequent to the AFM treatment, the residual density \( n_{t,0} \) is indeed reduced substantially and the mobility \( \mu \) is enhanced as well. The ratio of these two quantities follows \( 1/\mu = (h/e) \times n_{t,0} \times 0.118 \) as predicted by the theoretical model of random strain fluctuations in the work of Couto et al. [19]. Here, \( h \) is Planck’s constant and \( e \) is the elementary charge.

Until now, we have discussed the notable improvement of the electrical properties and the quantum transport features at low temperature. Finally, we turn our attention to the impact of AFM ironing on the room temperature transport properties of graphene as relevant for applications. Among these potential applications are Hall sensors, which have been intensively studied in recent years as encapsulated graphene may offer exceptional sensitivity [29, 30, 31, 32]. Fig. 4 illustrates typical room temperature data recorded on a 500°C annealed and hBN-encapsulated graphene device (G2) before and after AFM treatment. Panel a displays the density dependence of the conductivity, \( \sigma(n) \). The density interval around the CNP for which the conductivity remains at its minimum narrows considerably after AFM ironing. The rise of the conductivity as we move away from the CNP also becomes steeper indicating that the mobility, mostly limited by long range disorder at low density, increases. Empirically, the somewhat non-linear density dependence of the conductivity can be described by a density-independent mobility due to long range scattering, \( \mu_{LR} \), and a density-independent resistivity related to short range scattering [16, 33]. Applying this model to the measured curves yields \( \mu_{LR} = 89,000 \text{ cm}^2/\text{Vs} \) before and \( \mu_{LR} = 167,000 \text{ cm}^2/\text{Vs} \) after the AFM treatment. These values were averaged
between the electron and hole side. This improvement by nearly a factor of 2 is remarkable for such a straightforward post-processing AFM cleaning step. Panel b of Figure 4 displays the density dependence of the field effect mobility, \( \mu_{\text{FE}} = \sigma / e n \), as well as of the Hall mobility, \( \mu_H = R_H \sigma \), before and after AFM cleaning. Here, \( R_H \) is the Hall coefficient. It has been obtained from measuring the transverse resistivity while sweeping the magnetic field in the classically weak regime (here +/- 50 mT) and is also displayed in panel c. Both expressions for the mobility assume that transport occurs via a single carrier type, which is not valid near the CNP where electrons and holes coexist. This is also apparent from the Hall coefficient. The maximum at negative voltage and the minimum at positive voltage demarcate the regime of coexisting electron and holes. In this regime, the field effect mobility diverges and the Hall mobility goes to zero at the CNP. The overall mobility enhancement subsequent to the AFM treatment is again clearly visible in panel b. The Hall coefficient surpasses 5000 \( \Omega/T \), the earlier reported record sensitivity [31]. Panel d in Fig. 4 summarizes the maximum Hall sensitivity achieved on AFM treated and encapsulated graphene devices in this work as well as devices not treated by AFM. This high value is reliable achieved, while non-treated devices perform on average weaker. Elsewhere, it has been demonstrated that the maximum Hall coefficient values are closely correlated to the residual total carrier density at the CNP \( n_t,0 \), since \( R_{H,\text{max}} = 1 / 2 e n_t,0 \) [30, 32]. For our best AFM ironed devices we find \( n_{t,0} \sim 6 \times 10^{10} \text{ cm}^2 \). Similar values can also be estimated from the conventional graphical analysis of a double-logarithmic diagram plotting the conductivity versus density [19, 34], as illustrated in Figure S2. These achieved values, \( R_{H,\text{max}} \) and \( n_{t,0} \), constitute intrinsic performance limits of graphene based Hall sensors due to thermal excitation of charge carriers at room temperature [30, 35, Section 4 of SI]. The post-processing AFM cleaning apparently enables to reach this intrinsic limit reliably. Charge inhomogeneity is no longer relevant, but instead the simultaneous presence of electrons and holes due to thermal excitation [34, 35]. We may anticipate that under these conditions scattering is no longer dominated by extrinsic disorder, but rather acoustic phonon scattering. This is confirmed in additional resistivity data in the supplementary information (Fig. S2 and S4).

In summary, the electrical properties of van der Waals heterostructures, that are receptive to self-cleansing effects, can be substantially and reliably augmented with post-processing AFM cleaning by exerting a constant force between 50 and 150 nN with the tip. Devices with initially poor performance can be healed. Not only low temperature, but also room temperature electrical characteristics, as relevant for some applications, are improved and frequently reach intrinsic limits set by the thermally excited charge carriers. Previous work has identified random strain fluctuations as the key remaining culprit for extrinsic disorder in otherwise clean and high quality heterostructures. It is therefore plausible to surmise that the AFM action should be thought of as ironing away small local corrugations at the heterointerfaces, thereby reducing the role of local strain fluctuations for transport scattering.
Figure 1. (a) Four terminal longitudinal resistance as a function of the gate voltage for device G1 in the absence of a magnetic field and $T = 1.3$ K. The inset shows a microscopic image of the device. The scale bar corresponds to 10 $\mu$m. Longitudinal resistivity (b) and Hall conductivity (c) as a function of gate voltage at $B = 1$ T and $T = 1.3$ K. The red and black lines show the results before and after the AFM ironing, respectively.
Figure 2. (a) Shubnikov-de Haas oscillations on device M1 with a density of $5 \times 10^{12}$ cm$^{-2}$ at $T = 1.7$ K. Red and black lines show results before and after contact mode AFM, respectively. The red magnetotransport curve is vertically offset (-0.5 kΩ) for clarity. The inset displays an optical image of the device. Black dotted line represents graphite as a top gate while the MoS$_2$ flake is indicated by the blue dotted line. The scale bar corresponds to 10 μm. (b) Magnified low magnetic field regime of (a). Black and red arrows mark the onset of Shubnikov-de Haas oscillations, whereas symmetry broken states are highlighted with blue arrows.
Figure 3. (a) Schematic of the van der Waals heterostructure device geometry and the AFM treatment. The bottom panels highlight the ironing effect. (b) Atomic force microscopy images of graphene based heterostructure G1 before (Left) and after (Right) AFM treatment. (c) Height profiles measured along the horizontal dashed lines in (b). Black curve is vertically offset with 1 nm for clarity. (d) Histogram of the height variation Δh in the areas demarcated by the boxes in (b). (e) Optical image of a van der Waals heterostructure before (left) and after (right) contact mode AFM. The heterostructure consists of a total of six 2D crystals: hBN, graphite, hBN, graphene, hBN, graphite (top to bottom). The area treated by the AFM as well as the scan direction have been imposed on the optical image. Three large bubbles are marked as A, B, and C. A has disappeared after the treatment, B has shrunk and C has moved. (f) AFM image recorded in non-contact mode of a hBN/MoS2/hBN van der Waals heterostructure before (left) and after (right) contact mode AFM cleaning. White areas on the left and right side of the flake correspond to Cr/Au electrodes. Large bubbles have shrunk in size, smaller ones have disappeared after AFM cleaning.
Figure 4. Room temperature transport measurements on graphene Hall bar device G2. (a) Conductivity as a function of gate controlled density before and after the AFM ironing step. The conductivity minimum at the CNP clearly narrows and the mobility increases. (b) Field effect mobility (solid lines) and Hall mobility (dotted lines) derived from the conductivity and Hall coefficient measurements. (c) Hall coefficient measured in weak magnetic fields as a function of gate voltage. The top axis shows the corresponding carrier density assuming a single carrier type. After the AFM treatment, substantially larger maximum Hall coefficients are obtained. These Hall coefficients correspond to the Hall sensor sensitivity. (d) Maximum Hall coefficients of a large ensemble of graphene devices. Each data point was recorded on a separate device. Black data points were obtained on hBN-encapsulated devices that were manufactured according to the full cleaning protocol, consisting of a 500°C annealing step before device processing and an AFM treatment afterwards. Red data points are hBN-encapsulated devices that were annealed but no contact AFM step was performed. For the devices shown, the annealing temperature before device processing ranged from 200°C up to 500°C. We found a slight improvement with increasing temperature but the impact is much smaller than the AFM treatment itself. Green data points correspond to uncovered graphene devices on SiO₂/Si substrates. They serve as reference. The mean values and standard deviations for each device type have been included as a circle with error bar in the respective color.
**Associated Content**

**Supporting Information**

Increase of bubble free area by annealing, importance of 500°C anneal for significant quality enhancement upon AFM ironing, low temperature conductivity measurements and residual density estimates on additional graphene devices, and device statistics for key room temperature figure of merits using different processing protocols

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**Author Contributions**

Y.K., P.H., and J.H.S. conceived the project. Y. K. and P.H. carried out the device fabrication and performed the electrical measurements. T.T and K.W synthesized the h-BN crystal. Y.K., P.H, and J.H.S wrote the manuscript.

**Notes**

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**References**


Supporting Information for

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S1. Increase of bubble free area by annealing

To illustrate the beneficial effect of thermal annealing, we provide dark field optical images of a hBN-graphene-hBN van der Waals heterostructure immediately after stacking as well as after two subsequent annealing steps. The first anneal is performed at 350°C and a second anneal proceeds at 500°C. With increasing annealing temperature, the bubbles merge and almost completely disappear during the final annealing step of 500°C. Non-contact AFM measurements also show that the remaining area is mostly free from bubbles (but not necessarily from sub-nanometer interfacial roughness that cannot be measured). Hence, the available area for designing the device is substantially increased. The graphene device G2, discussed in the main text, was manufactured from the stack shown here.

Figure S1. Dark field images of a hBN-graphene-hBN stack after fabrication and annealing (size of the marker consisting of two parallel lines at the bottom left is 5 µm). Light intensity in the right image, after 500°C annealing, was increased but no bubbles are visible. Instead, larger wrinkles form mostly along the edges of the graphene flake. However, those wrinkles do not reduce the available area for the device.
S2. Importance of 500°C anneal for significant quality enhancement upon AFM ironing

We find that for graphene as the active layer, an AFM treatment after the device fabrication has been completed only reliably causes a substantial improvement of the properties, if after stacking and prior to device fabrication the van der Waals heterostructure is annealed at 500°C. For the sake of completeness we note that we also conduct a final annealing step at 350°C after complete device processing, just prior to the AFM step. Figure S2 demonstrates exemplary the importance of the high temperature annealing step at 500°C after stacking for two devices. The same observations were also made on other devices.

**Figure S2.** Room temperature magnetotransport measurements on two different hBN-encapsulated graphene devices before and after the AFM ironing step. Panel a-c: Resistivity, conductivity and Hall coefficient recorded on device G2. This device has been annealed at 500°C after stacking. It has already been discussed in Fig. 3 of the main text. Panels d-f: Same as for panel a-c but for a device that has been annealed only up to 350°C. For both devices another 350°C annealing step was performed after device processing. Only the first device shows a substantial improvement of the transport properties upon AFM ironing.
S3. Low temperature conductivity measurements and residual density estimates on additional graphene devices

Figure S3 plots the conductivity as a function of density on a double log scale at 1.3 K recorded before and after contact mode AFM on three graphene devices (device G1, G3, and G4). Device G1 is the same device as discussed in the main text. The residual density typically drops down to $10^{10}$ cm$^{-2}$ or below consistent with the picture that random strain fluctuations are reduced by the AFM treatment.

**Figure S3.** Conductivity as a function of density on a double logarithmic scale for device G1 (Left), G3 (middle) and G4 (right). These data have been recorded at 1.3 K. Red and black lines are measurements before and after contact mode AFM, respectively. Dotted lines are for electron transport and solid lines for hole transport. Arrows mark the estimated residual charge carrier density as determined from the crossing of a linear extrapolation of the conductivity at high density and the conductivity saturation at low density. Device images are displayed in the inset of each panel. The scale bars correspond to 10 μm scale bar. The image for device G1 image can be found in panel a of Fig. 1.
S4. Device statistics for key room temperature figure of merits using different processing protocols

We compare key transport characteristics for different device fabrication protocols and demonstrate that the combination of a 500°C anneal after stacking and a post-processing AFM treatment reliably yields the best results. Panels a through e of Fig. S4 display the resistivity maximum at the CNP, the residual density at the CNP as estimated from a log-log plot of the conductivity versus density, the resistivity at a high density of $n = 10^{12}$ cm$^{-2}$ where only one carrier type is present and the mobility at this density, respectively. Each data point in every panel of Figure S4 corresponds to an individual device. Data points have been grouped into three columns. The first column reports data for devices fabricated out of bare graphene supported on SiO$_2$ without any additional treatment. These green data points serve as reference. All other devices consist of graphene flakes encapsulated in between two hBN flakes. Data on devices that were annealed at a maximum temperature of 350°C without conducting the final AFM treatment were plotted in the second column. Finally, the black data points in the third column were gathered on encapsulated graphene that underwent a 500°C anneal after stacking and AFM ironing after device processing. In all cases, the doped silicon substrate served as the back gate for tuning the carrier density. Figure S4 clearly shows that the transport properties are significantly and reliably enhanced using the fabrication and AFM cleaning method outlined before. This becomes particularly apparent when adding an average of the data points and their standard deviation for each plotted quantity and processing protocol (square symbol and error bar). The variation among the data points has shrunk significantly for AFM treated samples. As discussed in Section S2, the AFM ironing does not lead to a notable improvement of the sample characteristics, if a van der Waals heterostructure is only annealed up to 350°C or less (This case is not shown in Fig. S4).

The dashed line in panel b marks the thermally excited total density at room temperature (300K) assuming a linear energy dispersion with Fermi velocity $v_F = 10^6$ m/s. It can be calculated analytically and reads $n_{t,0}(T) = (\pi k_B^2 / 3 \hbar^2 v_F^2) T^2$ [34, 35]. The experimentally obtained values are substantially smaller confirming previous studies that $v_F$ is larger in high quality devices due to renormalization effects (see also Ref. [35]). The acoustic phonon scattering limits [4, 36] have been included in panels d and e as grey shaded areas. At high carrier density this acoustic phonon limit is approached. Hence, we conclude that the post-processing AFM cleaned devices approach the intrinsic limit. There is also a clear correlation between the drop in the residual carrier density for the high quality AFM treated devices and the measured maximum in the Hall coefficient, proving the relation $R_{H,max} = 1 / 2 e n_{t,0}$ (see Figure 3d in the main text). Finally, supported by the statistics we have collected here, we are able to stipulate empirical criteria to identify high quality devices at room temperature based on two quick measurements: the resistivity at the CNP and the resistivity in the high density limit (here $n = 10^{12}$ cm$^{-2}$). The peak resistivity at the CNP should be around 1kΩ and the resistivity at high density below 100 Ω, better 50-70 Ω, or as a rule of thumb at least 1/10 of the peak resistivity.

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Figure S4. Statistics of the electrical transport properties of bare graphene and encapsulated graphene devices measured at room temperature. We distinguish between bare graphene devices on SiO$_2$ (green), hBN-encapsulated graphene devices annealed at 350°C without AFM treatment (red), as well as encapsulated devices which were annealed at 500°C after stacking and treated with AFM after the device processing has been completed (black data points). The data points for these three sets of devices are organized in three columns in each panel. Squares with error bars represent the average value of the plotted quantity and its standard deviation. (a) Maximum resistivity at the CNP as extracted from the resistivity curve as a function of the applied gate voltage. (b) Residual total carrier density at the CNP, as estimated from the double-logarithmic plot of the conductivity as a function of density (see panel b of Figure S2). The dashed line marks the thermal limit for a linear band structure dispersion with $v_F = 10^6$ m/s. (c) Estimate of the mobility at the CNP, using $\mu_{\text{CNP}} = 1 / (e n_{\text{CNP}} \rho_{\text{max}})$. (d) Resistivity at a carrier density of $n = 10^{12}$ cm$^{-2}$. At this density only one carrier type is present. (e) Mobility at $n = 10^{12}$ cm$^{-2}$, derived from the resistivity value. Gray shaded areas in panels d and e mark the limit due to acoustic phonon scattering [4, 36, 37]. Note the logarithmic scale in panels c to e. The gate voltage to density conversion factors were determined from separate Hall measurements on each device.